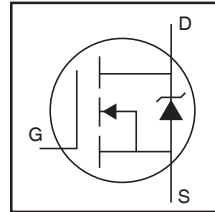


AUIRFP4004

HEXFET® Power MOSFET

Features

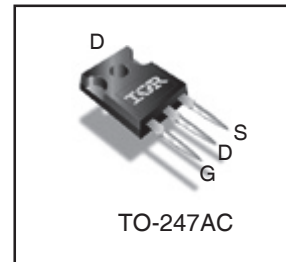
- Advanced Process Technology
- Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}	40V
$R_{DS(on)}$ typ.	1.35mΩ
max.	1.70mΩ
I_D (Silicon Limited)	350A^①
I_D (Package Limited)	195A

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	350 ^①	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	250 ^①	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	195	
I_{DM}	Pulsed Drain Current ^②	1390	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	380	W
	Linear Derating Factor	2.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally limited) ^③	290	mJ
I_{AR}	Avalanche Current ^②	See Fig. 14, 15, 21a, 21b	A
E_{AR}	Repetitive Avalanche Energy ^⑤		mJ
dv/dt	Peak Diode Recovery ^④	2.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ^⑥	—	0.40	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient ^⑧	—	40	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/°C	Reference to 25°C , $I_D = 5mA$ ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.35	1.70	mΩ	$V_{GS} = 10V, I_D = 195A$ ⑤
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	290	—	—	S	$V_{DS} = 10V, I_D = 195A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	220	330	nC	$I_D = 195A$
Q_{gs}	Gate-to-Source Charge	—	59	—		$V_{DS} = 20V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	75	—		$V_{GS} = 10V$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	145	—		$I_D = 195A, V_{DS} = 0V, V_{GS} = 10V$
$R_{G(int)}$	Internal Gate Resistance	—	6.8	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	59	—	ns	$V_{DD} = 20V$
t_r	Rise Time	—	370	—		$I_D = 195A$
$t_{d(off)}$	Turn-Off Delay Time	—	160	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	190	—		$V_{GS} = 10V$ ⑤
C_{iss}	Input Capacitance	—	8920	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	2360	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	930	—		$f = 1.0MHz$
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	2860	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 32V$ ⑦
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)	—	3110	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 32V$ ⑥

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	350①	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ② ⑦	—	—	1390		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 195A, V_{GS} = 0V$ ⑤
t_{rr}	Reverse Recovery Time	—	83	130	ns	$T_J = 25^\circ\text{C}$ $V_R = 20V,$
		—	78	120		$T_J = 125^\circ\text{C}$ $I_F = 195A$
Q_{rr}	Reverse Recovery Charge	—	190	290	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ⑤
		—	210	320		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	4.0	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 195A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. Refer to App Notes (AN-1140).
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.015mH$
 $R_G = 25\Omega$, $I_{AS} = 195A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ④ $I_{SD} \leq 195A$, $di/dt \leq 690A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ⑤ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑥ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑨ R_θ is measured at T_J approximately 90°C .

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		3L-TO-247	N/A
ESD	Machine Model	Class M4(+/- 800V) ^{†††} (per AEC-Q101-002)	
	Human Body Model	Class H3A(+/- 6000V) ^{†††} (per AEC-Q101-001)	
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

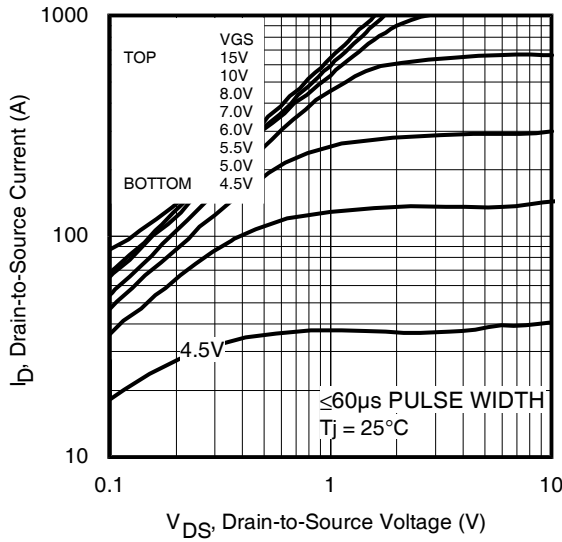


Fig 1. Typical Output Characteristics

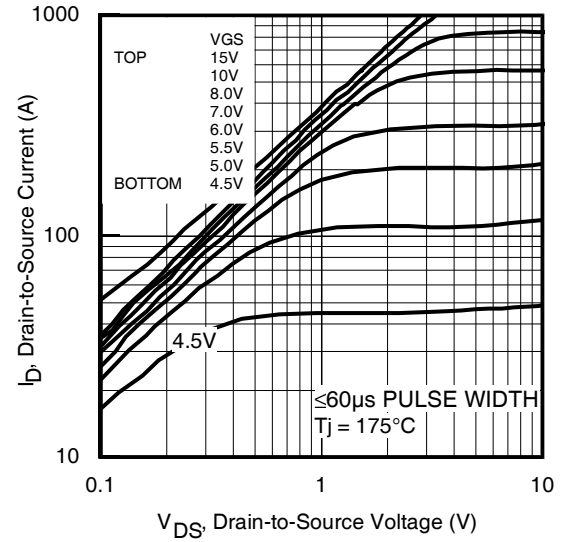


Fig 2. Typical Output Characteristics

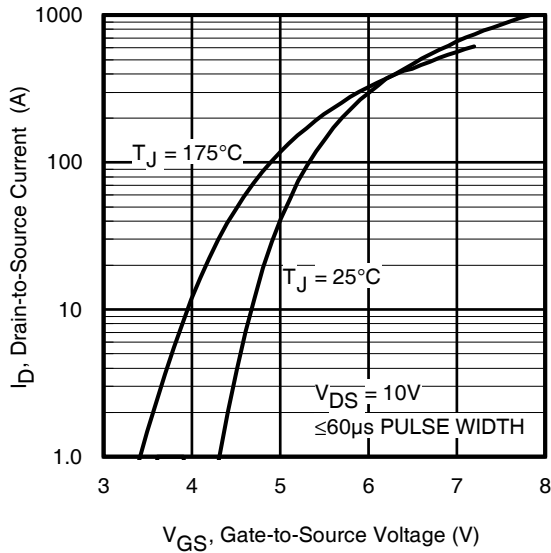


Fig 3. Typical Transfer Characteristics

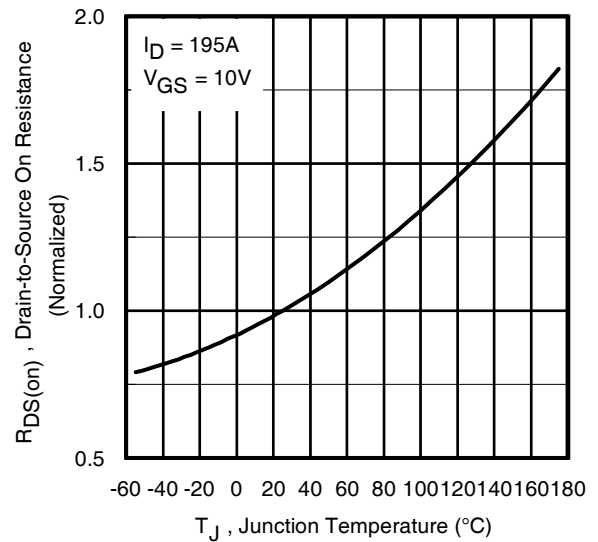


Fig 4. Normalized On-Resistance vs. Temperature

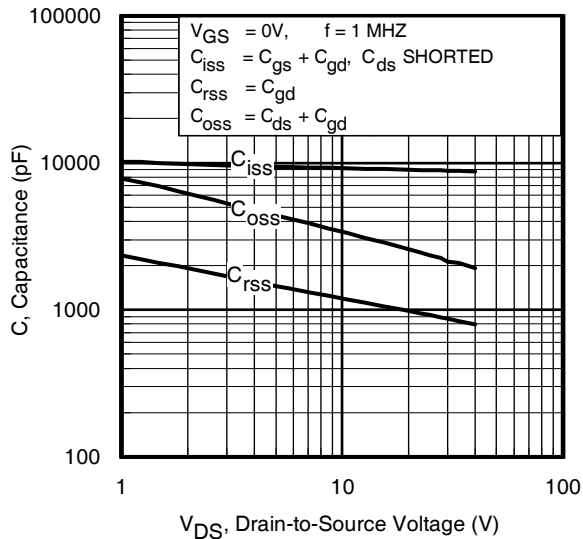


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

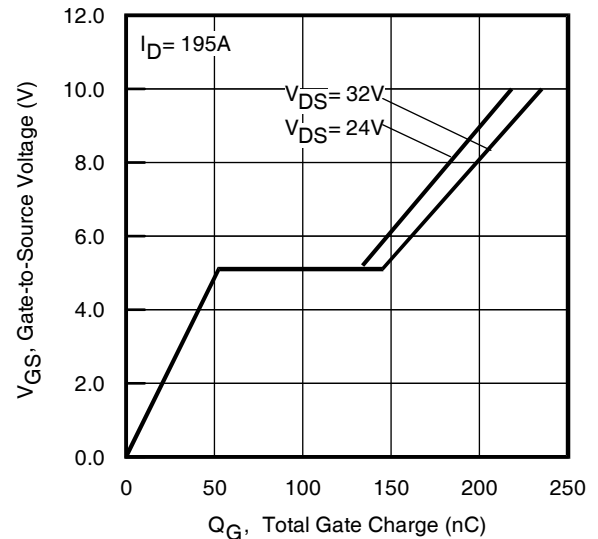


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

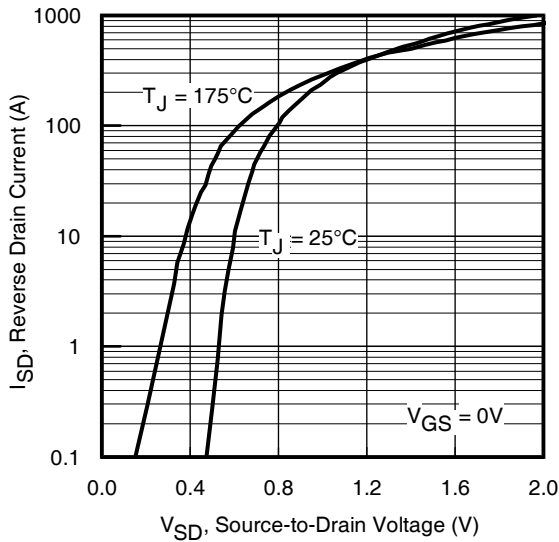


Fig 7. Typical Source-Drain Diode Forward Voltage

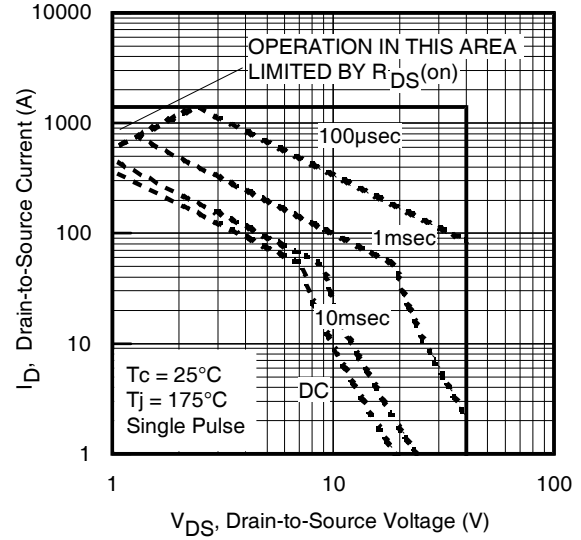


Fig 8. Maximum Safe Operating Area

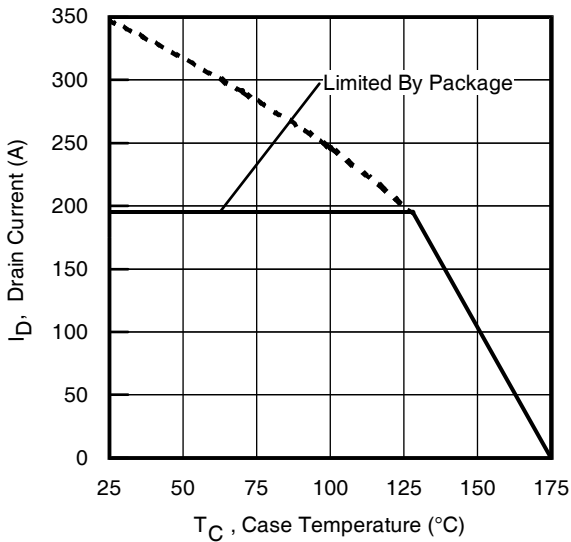


Fig 9. Maximum Drain Current vs. Case Temperature

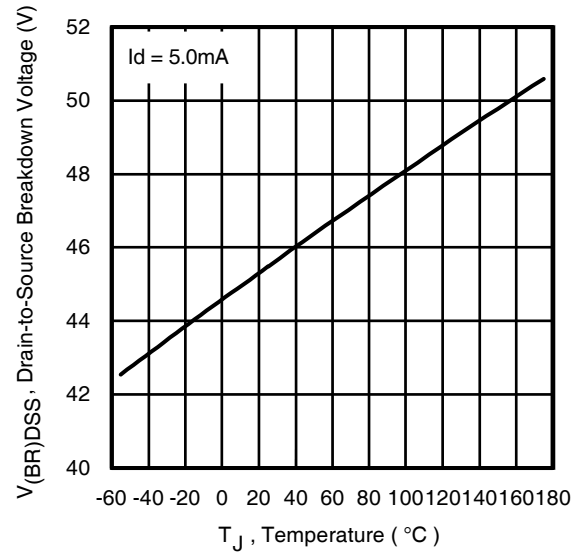


Fig 10. Drain-to-Source Breakdown Voltage

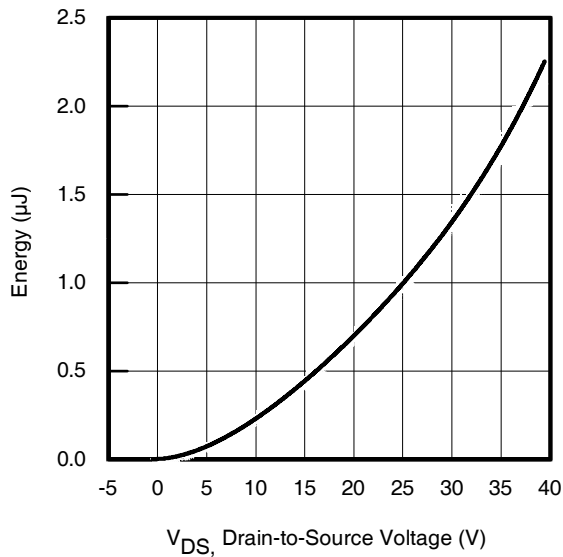


Fig 11. Typical C_{OSS} Stored Energy

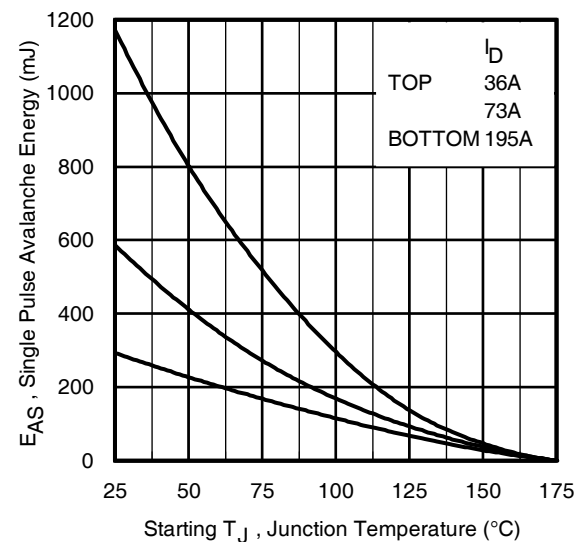


Fig 12. Maximum Avalanche Energy vs. Drain Current

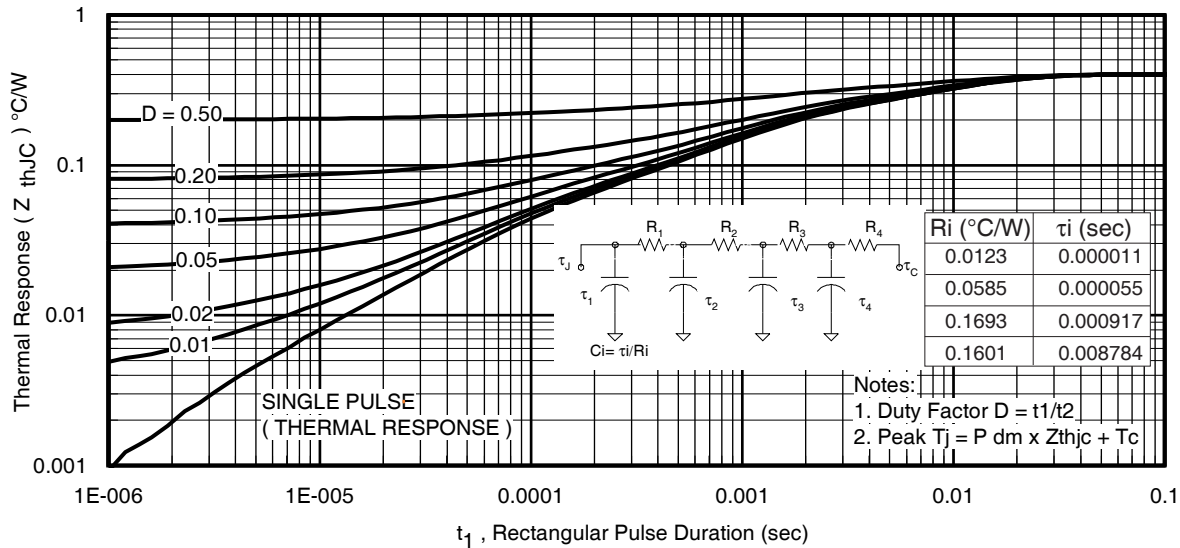


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

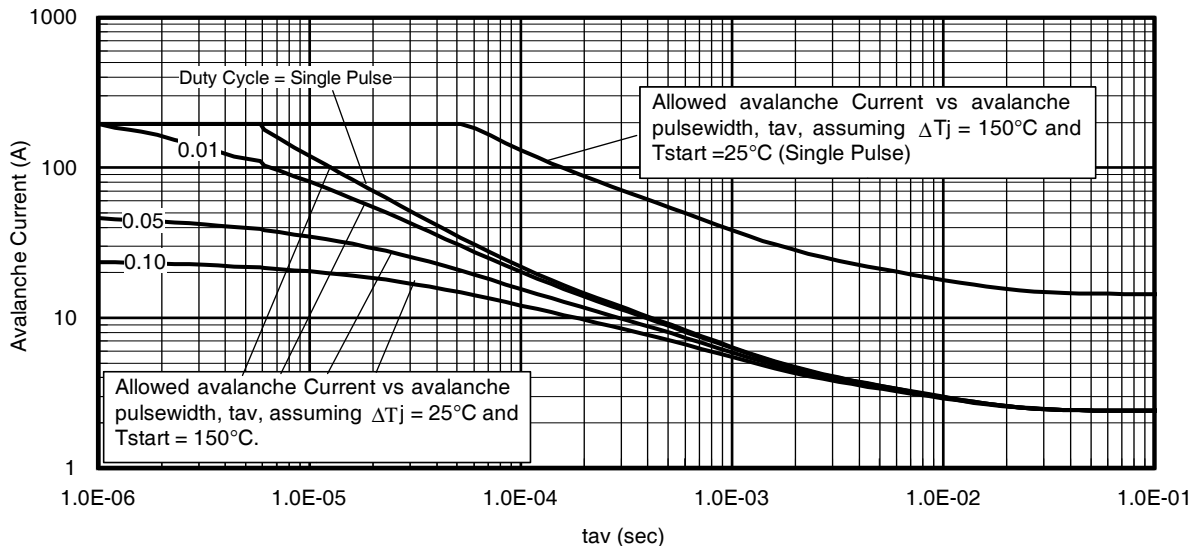


Fig 14. Typical Avalanche Current vs. Pulsewidth

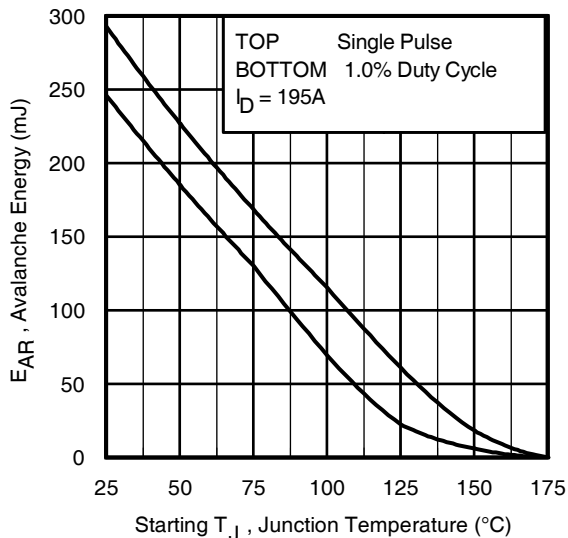


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 21a, 21b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

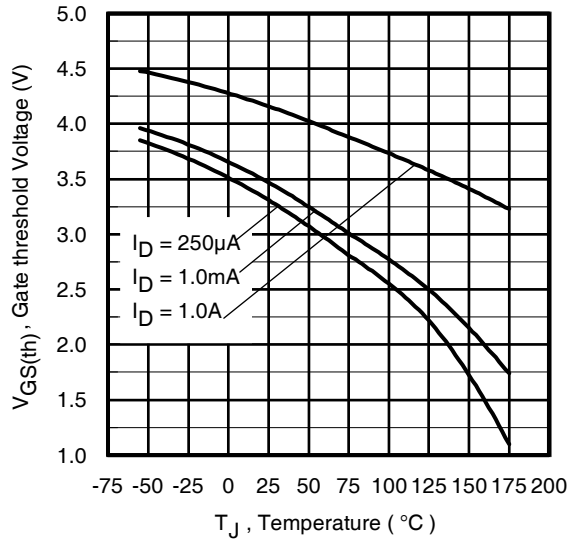


Fig. 16. Threshold Voltage vs. Temperature

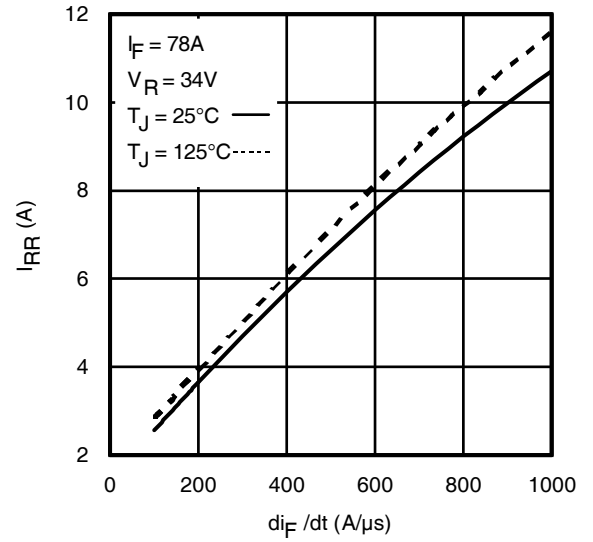


Fig. 17 - Typical Recovery Current vs. di_F/dt

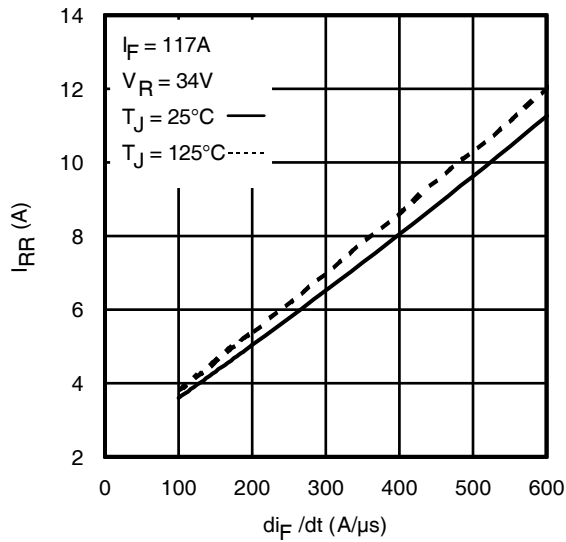


Fig. 18 - Typical Recovery Current vs. di_F/dt

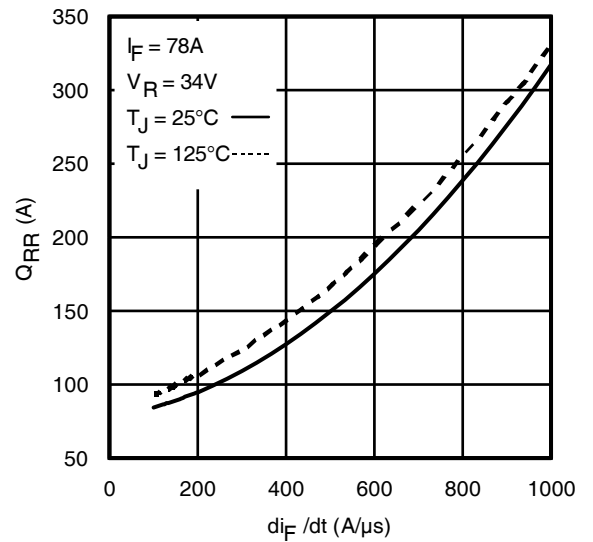


Fig. 19 - Typical Stored Charge vs. di_F/dt

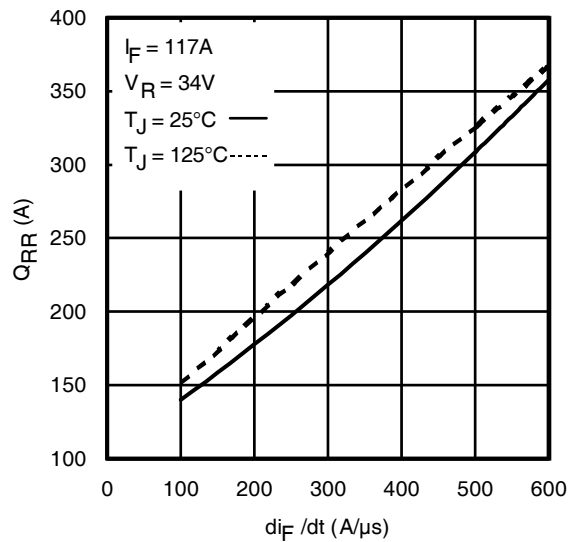


Fig. 20 - Typical Stored Charge vs. di_F/dt

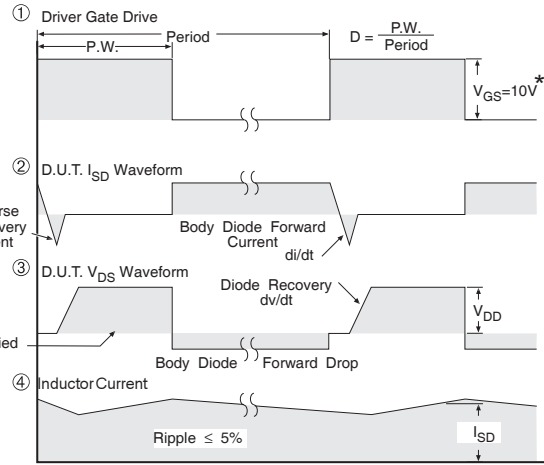
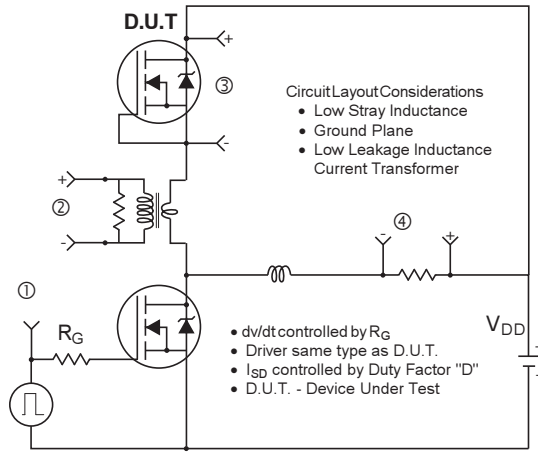


Fig 20. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

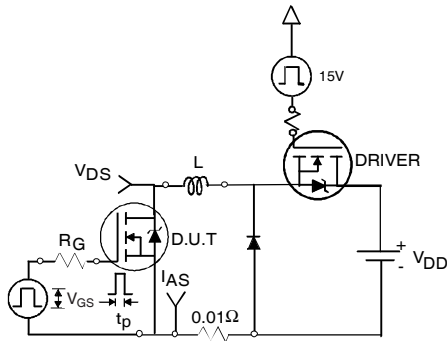


Fig 21a. Unclamped Inductive Test Circuit

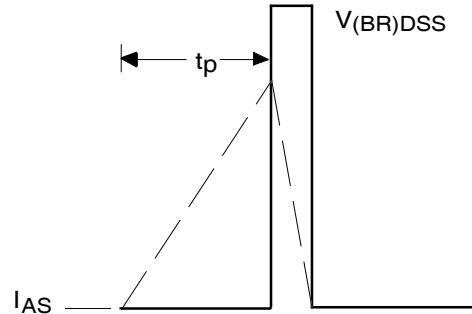


Fig 21b. Unclamped Inductive Waveforms

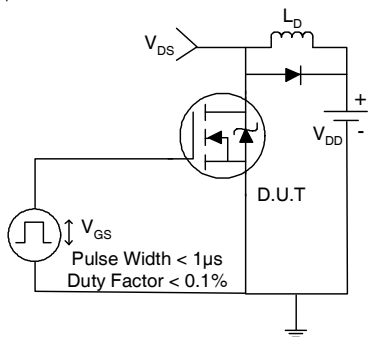


Fig 22a. Switching Time Test Circuit

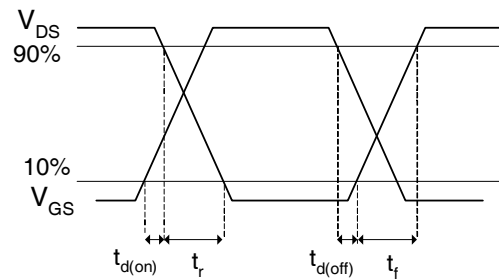


Fig 22b. Switching Time Waveforms

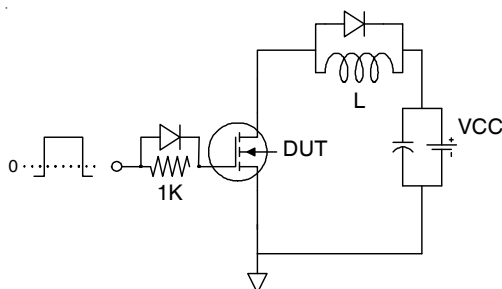


Fig 23a. Gate Charge Test Circuit

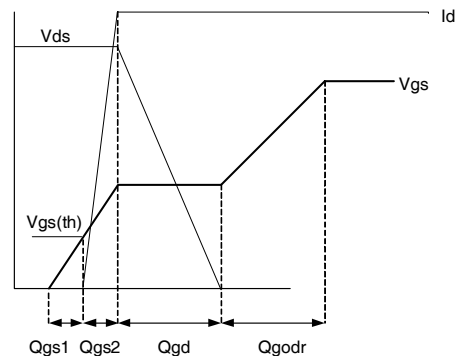
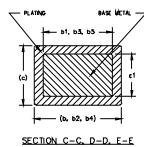
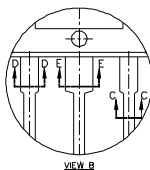
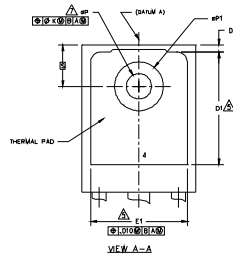
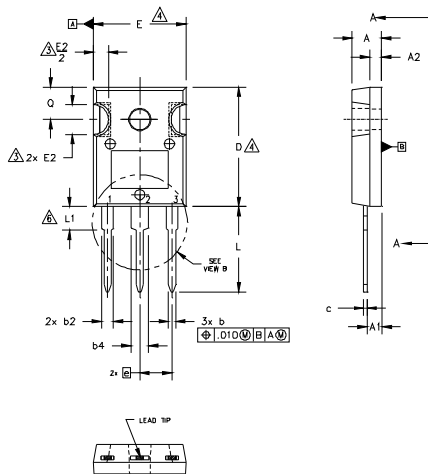


Fig 23b. Gate Charge Waveform

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

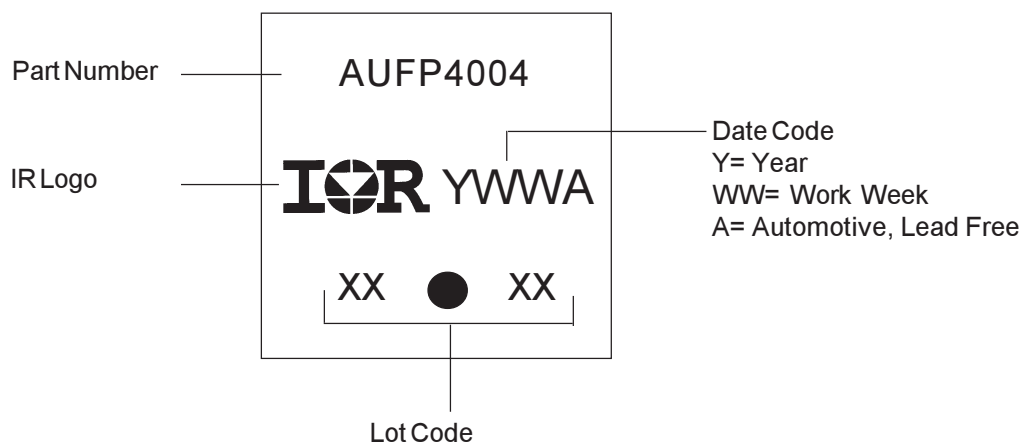
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information



Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFP4004	TO-247	Tube	25	AUIRFP4004

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For technical support, please contact IR’s Technical Assistance Center

<http://www.irf.com/technical-info/>

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